



HC2312

20V N-Channel MOSFET

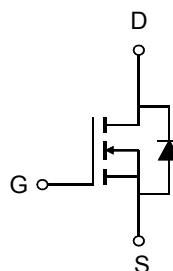
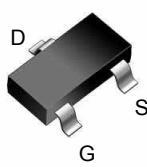
General Description

The HC2312 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

Features

V_{DS}	20V
I_D (at $V_{GS}=4.5V$)	6.8A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	13.5mΩ(Typ)

SOT23



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D (TC=25°C)	6.8	A
	I_D (TC=70°C)	5.4	A
Drain Current – Pulsed	I_{DM}	27	A
Maximum Power Dissipation	P_D	1.56	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C
Thermal Characteristics			
Parameter	Symbol	Typ	Max
Thermal Resistance junction-case	$R_{\theta JC}$		1.1 °C /W
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		62 °C /W

Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.65	1.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=4.5V, I_D=3.0A$		13.5	18	$m\Omega$
		$V_{GS}=2.5V, I_D=2.0A$		17	22	$m\Omega$
		$V_{GS}=1.8V, I_D=2.7A$		22	39	$m\Omega$
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=4.5A$		10		S
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, F=1.0MHz$		860		pF
C_{oss}	Output Capacitance			130		pF
C_{rss}	Reverse Transfer Capacitance			110		pF
SWITCHING PARAMETERS						
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=4.5V$ $V_{DS}=10V$ $R_G=25\Omega$ $I_D=6.8A$		7		nS
t_r	Turn-on Rise Time			46		nS
$t_{d(off)}$	Turn-Off Delay Time			30		nS
t_f	Turn-Off Fall Time			52		nS
Q_g	Total Gate Charge	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$		11		nC
Q_{gs}	Gate-Source Charge			1.73		nC
Q_{gd}	Gate-Drain Charge			3.1		nC
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=1A$		0.70	1.3	V

Note:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

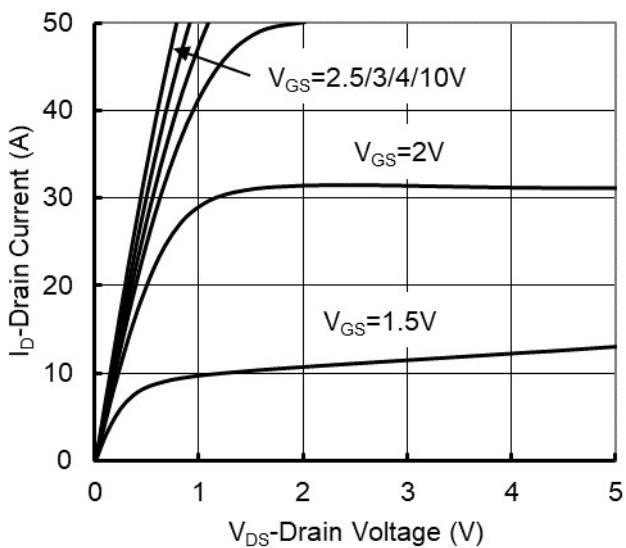


Figure 1. Output Characteristics

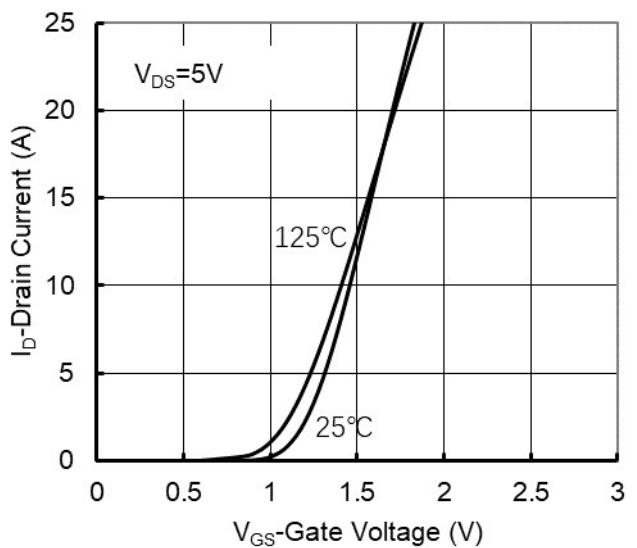


Figure 2. Transfer Characteristics

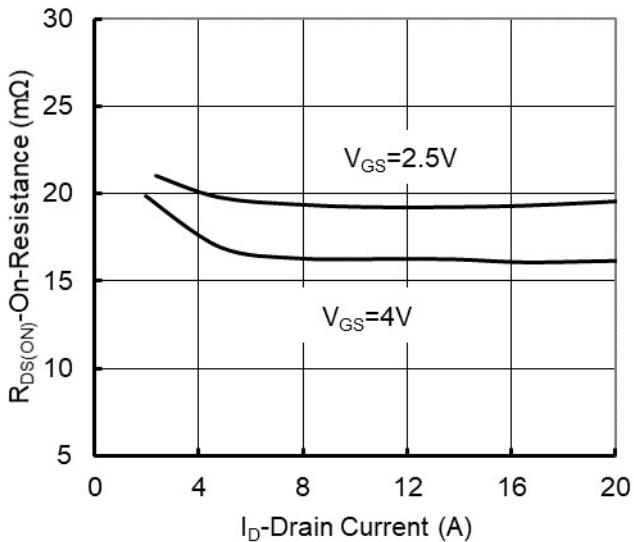


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

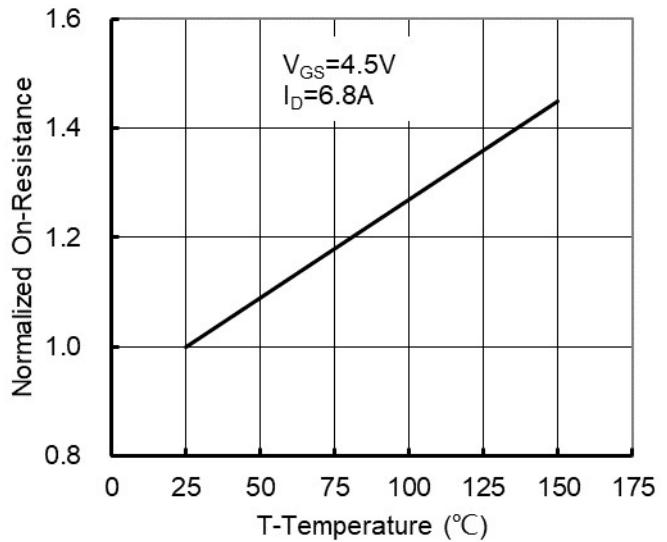


Figure 4: On-Resistance vs. Junction Temperature

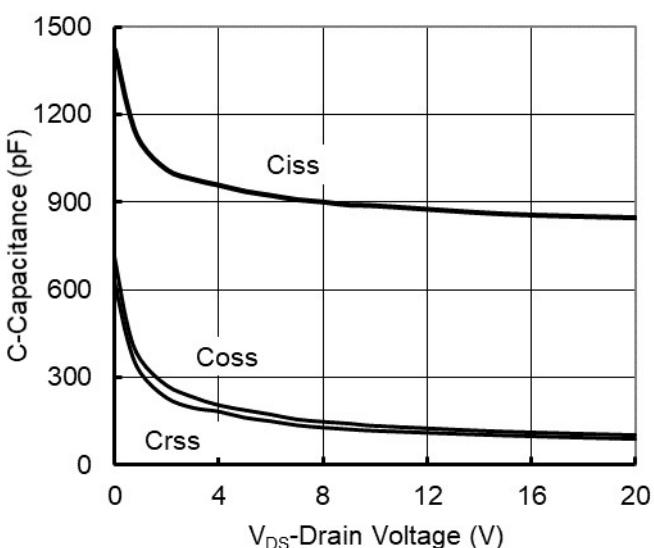


Figure 5. Capacitance Characteristics

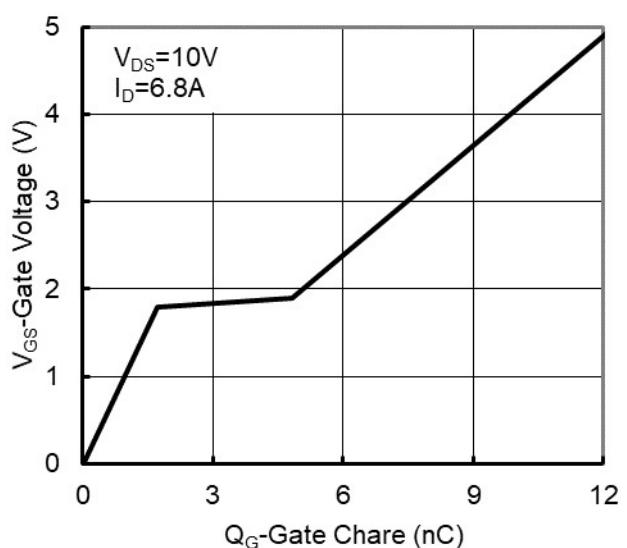


Figure 6. Gate Charge

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

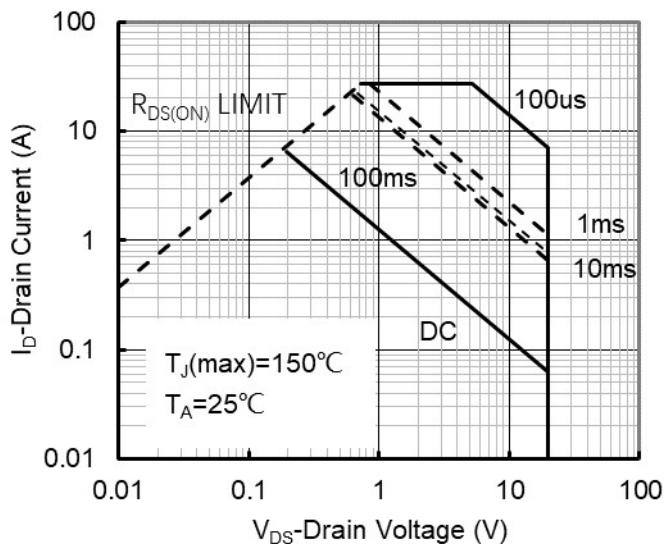


Figure 7. Safe Operation Area

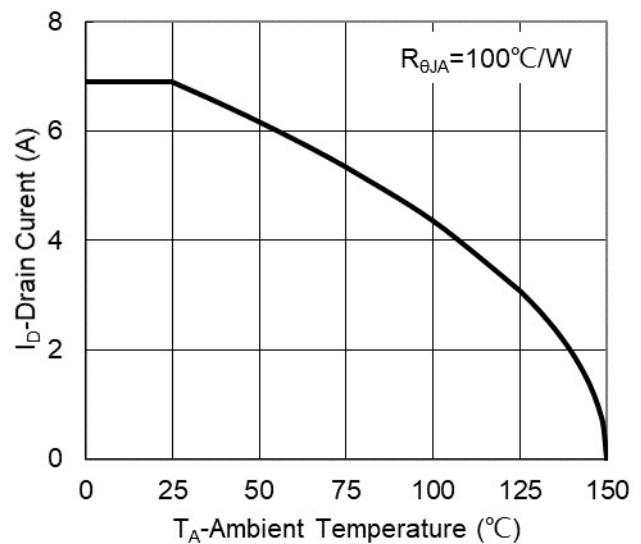


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

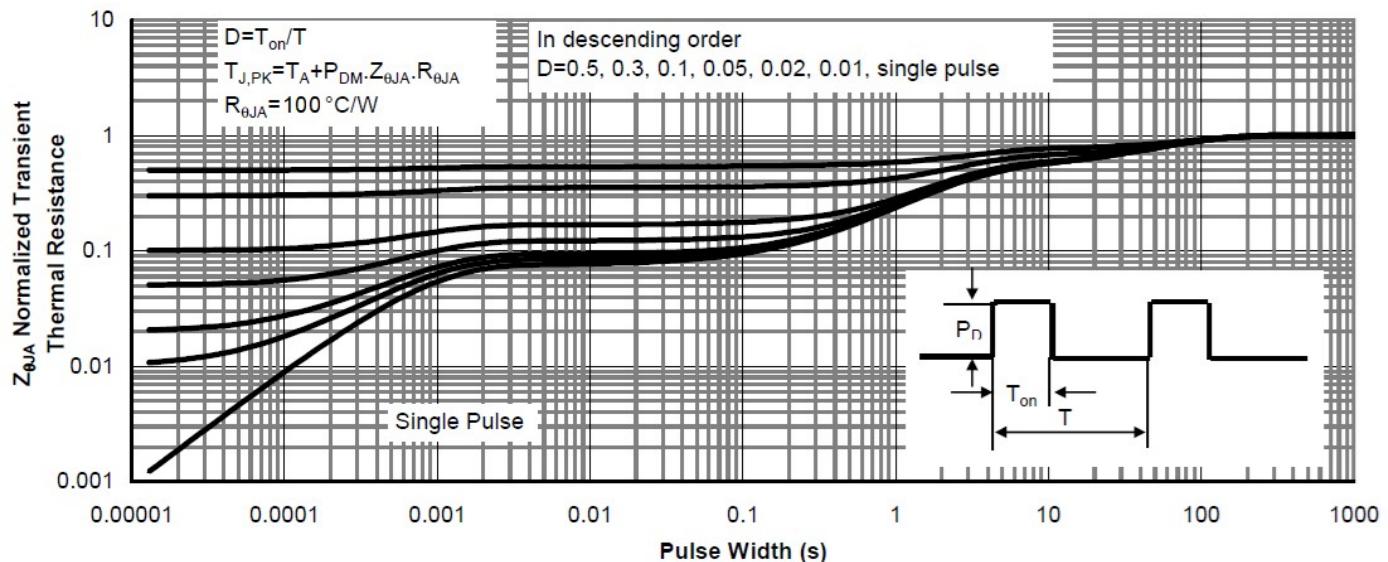
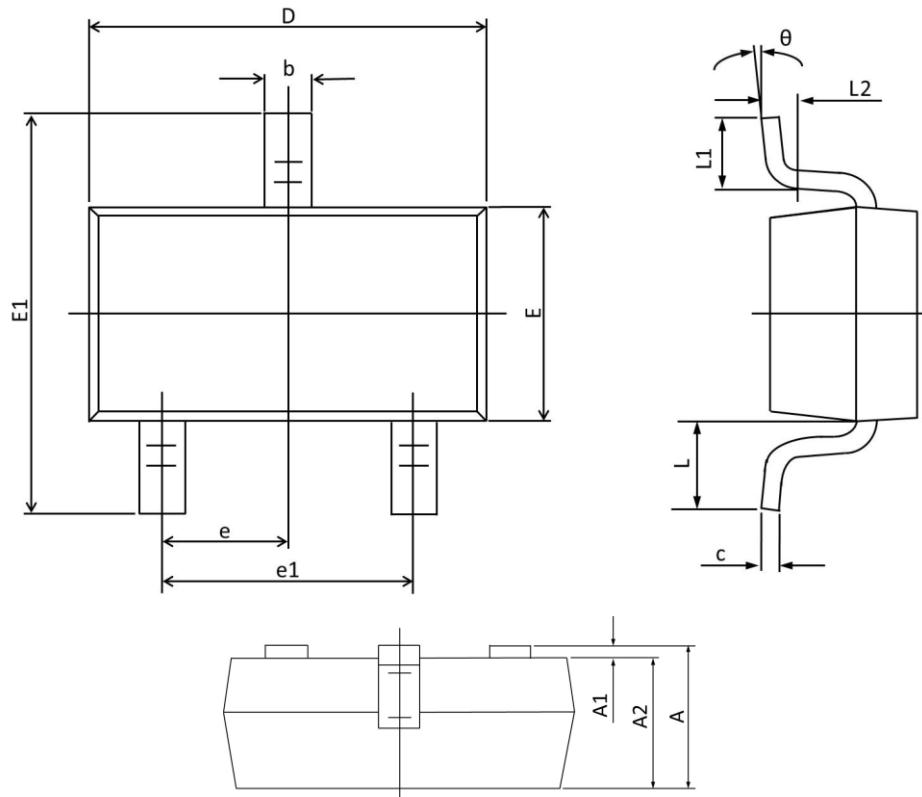


Figure 9. Normalized Maximum Transient Thermal Impedance

SOT23 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Max	Min	Max	Min
A	1.150	0.900	0.045	0.035
A1	0.100	0.000	0.004	0.000
A2	1.050	0.900	0.041	0.035
b	0.500	0.300	0.020	0.012
c	0.150	0.080	0.006	0.003
D	3.000	2.800	0.118	0.110
E	1.400	1.200	0.055	0.047
E1	2.550	2.250	0.100	0.089
e	0.95 TYP.		0.037 TYP.	
e1	2.000	1.800	0.079	0.071
L	0.55 REF.		0.022 REF.	
L1	0.500	0.300	0.020	0.012
L2	0.25 TYP.		0.01 TYP.	
theta	8°	0°	8°	0°